4060K

40V N-Channel Trench Power MOSFET

Extremely Low RDS(on):
RDS(on) =7.2mΩ @VGS=10 V, Id=40 A

试用水印 试用水印 试用水印

Features

- Good stability and uniformity
- 100% avalanche tested
- Excellent package for good heat dissipation

Package



TO-252

试用水印 试用水印 试用水印

Absolute Maximum Ratings (T_C=25℃unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	TC = 25℃	60	A
		TC = 100℃	42	A
I_{DM}	Pulsed Drain Current		240	A
E_{AS}	Single Pulsed Avalanche Energy		186	J
P_D	Power Dissipation	TC = 25℃	64	W
			0.68	W/℃
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.02	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

试用水印 试用水印 试用水印

www.superchip.cn